TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

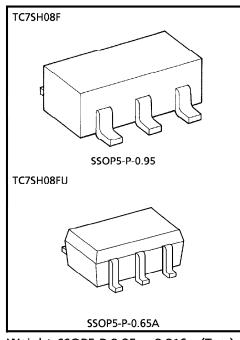
# TC7SH08F, TC7SH08FU

# 2-INPUT AND GATE

The TC7SH08 is an advanced high speed CMOS 2-INPUT AND GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 4 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interfase 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

#### **FEATURES**

- High Speed  $\cdots$   $t_{pd} = 4.3$ ns (Typ.) at  $V_{CC} = 5V$
- Low Power Dissipation  $\cdots I_{CC} = 2\mu A$  (Max.) at
- High Noise Immunity ················ V<sub>NIH</sub> = V<sub>NIL</sub>
  = 28% V<sub>CC</sub> (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······· t<sub>pLH</sub>≒t<sub>pHL</sub>
- Wide Operating Voltage Range····· V<sub>CC (opr)</sub> = 2~5.5V

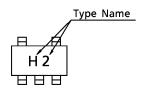


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

#### **MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	Vcc	- 0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	٧
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> +0.5	V
Input Diode Current	ΙΚ	- 20	mΑ
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 25	mA
DC V <sub>CC</sub> /Ground Current	Icc	± 50	mA
Power Dissipation	PD	200	mW
Storage Temperature	T <sub>stg</sub>	<b>-65∼150</b>	°C
Lead Temperature (10s)	TL	260	°C

#### MARKING



TRUTH TABLE

А	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

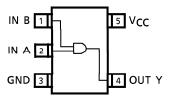
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#### **LOGIC DIAGRAM**



## PIN ASSIGNMENT (TOP VIEW)



#### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>CC</sub>	2.0~5.5	V
Input Voltage	VIN	0~5.5	٧
Output Voltage	Vout	0~V <sub>CC</sub>	٧
Operating Temperature T <sub>opr</sub>		<b>- 40∼85</b>	°C
Input Disc and Fall Time	d /d	$0\sim100 \text{ (V}_{CC}=3.3\pm0.3\text{V)}$	ns /\/
Input Rise and Fall Time	d <sub>t</sub> /d <sub>v</sub>	$0\sim 20 \ (V_{CC} = 5 \pm 0.5V)$	ns/V

#### DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST YMBOL CIR-		TEST CONDITION _		Ta = 25°C		Ta = − 40~85°C		UNIT	
		CUIT	TEST CONDITION		Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	OINIT
High-Level Input				_		1.50	_	_	1.50	_	
Voltage	V <sub>IH</sub>	_				V <sub>C</sub> C ×0.7	_	<u> </u>	V <sub>C</sub> C ×0.7	_	V
Low-Level Input					2.0	_	_	0.50	_	0.50	
Voltage	V <sub>IL</sub>		_		3.0~ 5.5	_	_	V <sub>C</sub> C ×0.3	_	V <sub>C</sub> C × 0.3	V
	Voн		VIN = VIH		2.0	1.9	2.0	_	1.9	_	
High-Level		_		$I_{OH} = -50 \mu A$	3.0	2.9	3.0	—	2.9	_	
Output-Voltage					4.5	4.4	4.5	_	4.4	_	V
				$I_{OH} = -4mA$	3.0	2.58	_	—	2.48	_	
				$I_{OH} = -8mA$	4.5	3.94	1	—	3.80	_	
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50μA	2.0	_	0.0	0.1	<u> </u>	0.1	
Low-Level Output-Voltage					3.0	_	0.0	0.1	<b>—</b>	0.1	
	Vol	_			4.5	_	0.0	0.1	_	0.1	V
				$I_{OL} = 4mA$	3.0	_	_	0.36	—	0.44	
				$I_{OL} = 8mA$	4.5		_	0.36	_	0.44	
Input Leakage Current	IN		V <sub>IN</sub> = 5.5V or GND		0~ 5.5	_	_	± 0.1	_	± 1.0	
Quiescent Supply Current	l <sub>CC</sub>	_	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	2.0	_	20.0	$\mu$ A

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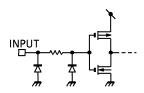
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## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

	TEST	TEST CO	TEST CONDITION			Ta = 25°C			Ta = −40~85°C		
PARAMETER SYMBOL	CIR- CUIT	1231 60	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	MIN.	TYP.	MAX.	-	MAX.	UNIT	
			_	3.3 ± 0.3	15	_	6.2	8.8	1.0	10.5	ns
	t <sub>PLH</sub>				50	_	8.7	12.3	1.0	14.0	
	t <sub>PHL</sub>			5.0 ± 0.5	15	_	4.3	5.9	1.0	7.0	
					50	_	5.8	7.9	1.0	9.0	
Input Capacitance	CIN	_	<u> </u>			_	4	10	_	10	
Power Dissipation Capacitance	C <sub>PD</sub>	_	Note (1)				14		_	_	pF

Note (1): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation : ICC (opr) = CPD·VCC·fIN + ICC

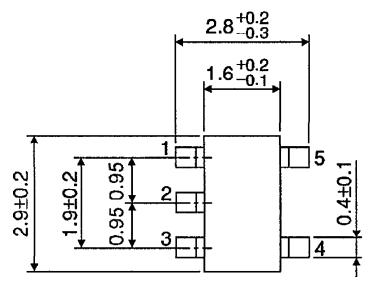
# INPUT EQUIVALENT CIRCUIT

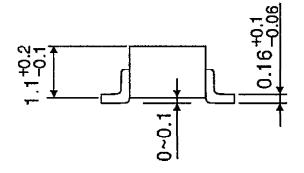


# OUTLINE DRAWING

SSOP5-P-0.95

Unit: mm

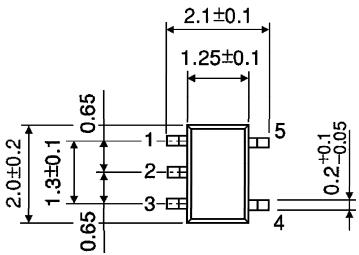




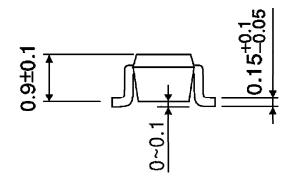
Weight: 0.016g (Typ.)

# **OUTLINE DRAWING**

SSOP5-P-0.65A



Unit: mm



Weight: 0.006g (Typ.)